

## CMSH9930Q8-HF

2N- and 2P-Channel

RoHS Device

Halogen Free



### Features

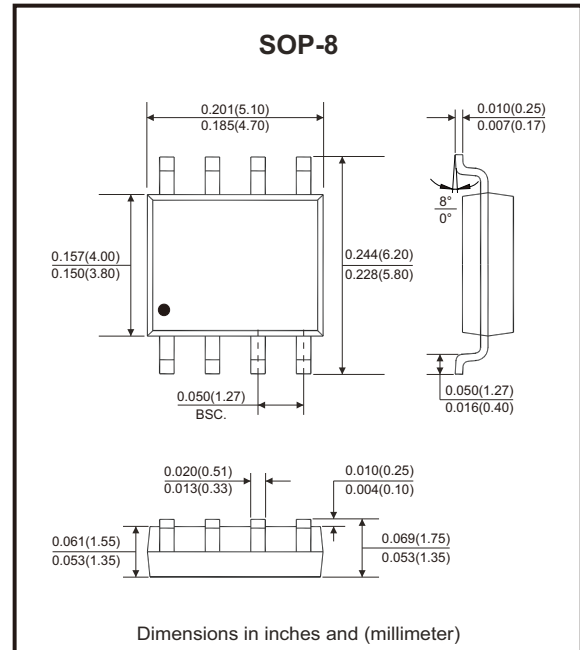
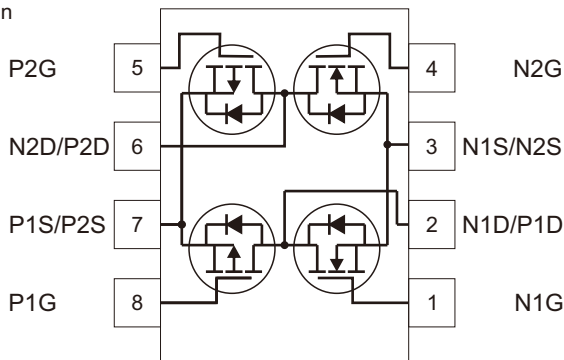
- Simple drive requirement.
- Low on-resistance.
- Fast switching speed.

### Mechanical data

- Case: SOP-8, molded plastic.
- Mounting position: Any.

### Circuit Diagram

G:Gate  
S:Source  
D:Drain



### Maximum Ratings (at TC=25°C unless otherwise noted)

Parameter	Symbol	N-Channel	P-Channel	Unit	
Drain-source breakdown voltage	$BV_{DSS}$	30	-30	V	
Gate-source voltage	$V_{GS}$	$\pm 20$	$\pm 20$	V	
Continuous drain current (Note 2)	$I_D$	$T_A = 25^\circ\text{C}, V_{GS} = 10\text{V} (-10\text{V})$	6	-4.4	A
		$T_A = 70^\circ\text{C}, V_{GS} = 10\text{V} (-10\text{V})$	4.8	-3.5	
Pulsed drain current (Note 1)	$I_{DM}$	24	-20	A	
Power dissipation	$P_D$	$T_A = 25^\circ\text{C}$	1.38		W
		$T_A = 70^\circ\text{C}$	0.88		
Max. thermal resistance, junction to case	$R_{\theta JC}$	36		$^\circ\text{C/W}$	
Max. thermal resistance, junction to ambient (Note 2)	$R_{\theta JA}$	90		$^\circ\text{C/W}$	
Operating junction and storage temperature range	$T_J, T_{STG}$	-55 to +150		$^\circ\text{C}$	

Notes: 1. Pulse width limited by maximum junction temperature.  
2. Surface mounted on 1in<sup>2</sup> copper pad of FR-4 board, pulse width  $\leq 10\text{s}$ .

## N-Channel Electrical Characteristics (at TC=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
<b>Static</b>						
Drain-source breakdown voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	30			V
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.0		2.5	V
Gate-source leakage	$I_{GSS}$	$V_{GS} = \pm 20, V_{DS} = 0V$			$\pm 100$	nA
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 30V, V_{GS} = 0V$			1	$\mu A$
		$V_{DS} = 24V, V_{GS} = 0V, T_J = 70^\circ C$			25	
Static Drain-source on-state resistance (Note 1)	$R_{DS(ON)}$	$I_D = 5A, V_{GS} = 10V$		17	24	m $\Omega$
		$I_D = 3A, V_{GS} = 4.5V$		21	30	
Forward transconductance (Note 1)	$G_{FS}$	$V_{DS} = 5V, I_D = 5A$		6.7		S
<b>Dynamic</b>						
Input capacitance	$C_{iss}$	$V_{DS} = 25V, V_{GS} = 0V, f = 1MHz$		496	750	pF
Output capacitance	$C_{oss}$			61		
Reverse transfer capacitance	$C_{riss}$			47		
Turn-on delay time (Note 1)	$t_{d(ON)}$	$V_{DS} = 15V, I_D = 1A, V_{GS} = 10V, R_G = 6\Omega$		6.2		ns
Rise time (Note 1)	$t_r$			17.2		
Turn-off delay time (Note 1)	$t_{d(OFF)}$			30.2		
Fall time (Note 1)	$t_f$			7.6		
Total gate charge (Note 1)	$Q_g$	$V_{DS} = 15V, I_D = 6A, V_{GS} = 4.5V$		5.6	9	nC
Gate-source charge (Note 1)	$Q_{gs}$			1.9		
Gate-drain charge (Note 1)	$Q_{gd}$			2.1		
<b>Body Diode</b>						
Diode forward voltage (Note 1)	$V_{SD}$	$V_{GS} = 0V, I_S = 1.2A$		0.78	1.2	V
Reverse recovery time (Note 1)	$t_{rr}$	$I_F = 5A, dI_F/dt = 100A/\mu s$		7.7		ns
Recovered charge (Note 1)	$Q_{rr}$				3.3	

Notes: 1. Pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .

## P-Channel Electrical Characteristics (at TC=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
<b>Static</b>						
Drain-source breakdown voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-30			V
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1.0		-2.5	V
Gate-source leakage	$I_{GSS}$	$V_{GS} = \pm 20, V_{DS} = 0V$			$\pm 100$	nA
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = -30V, V_{GS} = 0V$			-1	$\mu A$
		$V_{DS} = -24V, V_{GS} = 0V, T_J = 70^\circ C$			-25	
Static Drain-source on-state resistance (Note 1)	$R_{DS(ON)}$	$I_D = -4A, V_{GS} = -10V$		35	48	m $\Omega$
		$I_D = -2A, V_{GS} = -4.5V$		46	70	
Forward transconductance (Note 1)	$G_{FS}$	$V_{DS} = -10V, I_D = -5A$		7.8		S
<b>Dynamic</b>						
Input capacitance	$C_{iss}$	$V_{DS} = -25V, V_{GS} = 0V, f = 1MHz$		597	900	pF
Output capacitance	$C_{oss}$			63		
Reverse transfer capacitance	$C_{riss}$			51		
Turn-on delay time (Note 1)	$t_{d(ON)}$	$V_{DS} = -15V, I_D = -1A, V_{GS} = -10V, R_G = 6\Omega$		5.6		ns
Rise time (Note 1)	$t_r$			17.6		
Turn-off delay time (Note 1)	$t_{d(OFF)}$			64.4		
Fall time (Note 1)	$t_f$			33.8		
Total gate charge (Note 1)	$Q_g$	$V_{DS} = -15V, I_D = -4.4A, V_{GS} = -4.5V$		6.7	11	nC
Gate-source charge (Note 1)	$Q_{gs}$			2.2		
Gate-drain charge (Note 1)	$Q_{gd}$			2.5		
<b>Body Diode</b>						
Diode forward voltage (Note 1)	$V_{SD}$	$V_{GS} = 0V, I_S = -1.2A$		-0.78	-1.2	V
Reverse recovery time (Note 1)	$t_{rr}$	$I_F = -4.5A, dI_F/dt = 100A/\mu s$		7.7		ns
Recovered charge (Note 1)	$Q_{rr}$				3.0	

Notes: 1. Pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .

## N-Channel Typical Rating and Characteristic Curves (CMSH9930Q8-HF)

Fig.1 - Typical Output Characteristics

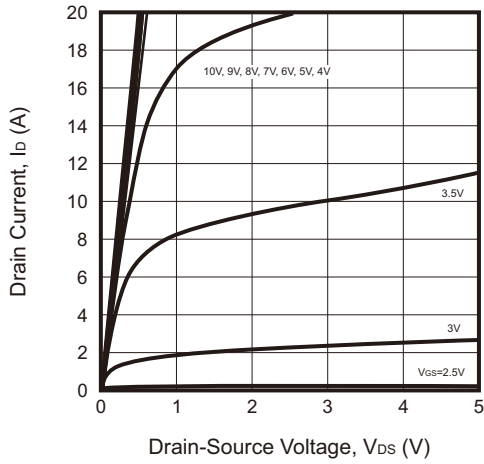


Fig.2 - Breakdown Voltage vs Ambient Temperature

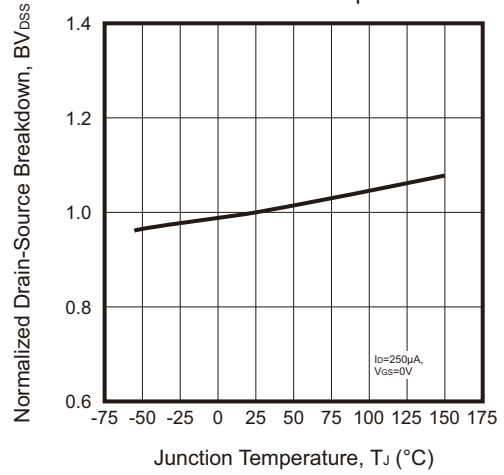


Fig.3 - Static Drain-Source On-State Resistance vs Drain Current

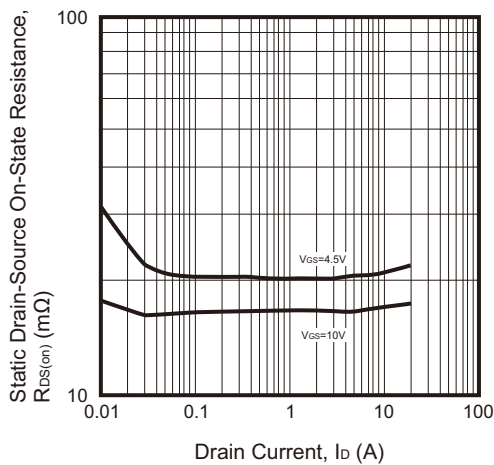


Fig.4 - Reverse Drain Current vs Source-Drain Voltage

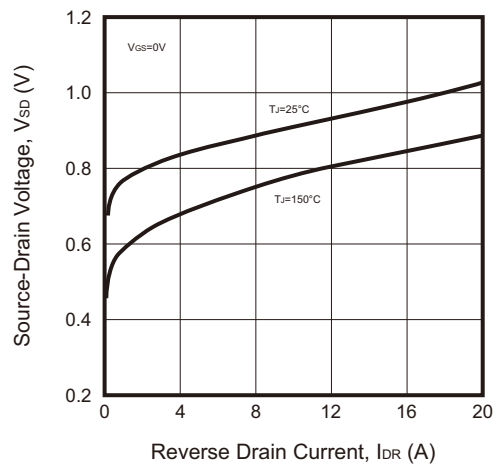


Fig.5 - Static Drain-Source On-State Resistance vs Gate-Source Voltage

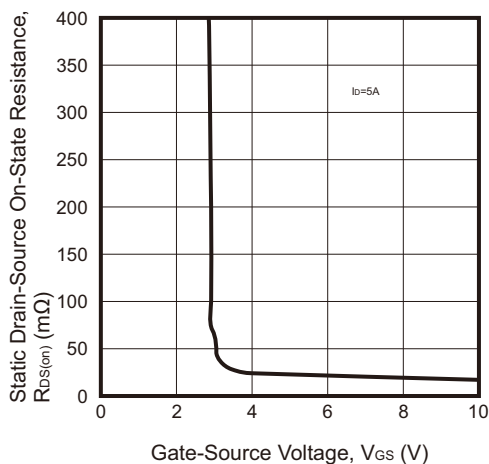
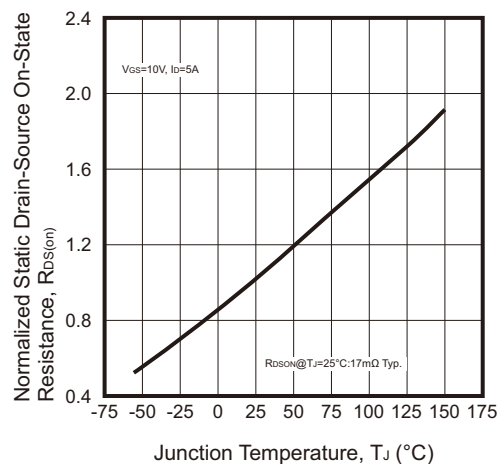


Fig.6 - Drain-Source On-State Resistance vs Junction Temperature



## N-Channel Typical Rating and Characteristic Curves (CMSh9930Q8-HF)

Fig.7 - Capacitance vs Drain-to-Source Voltage

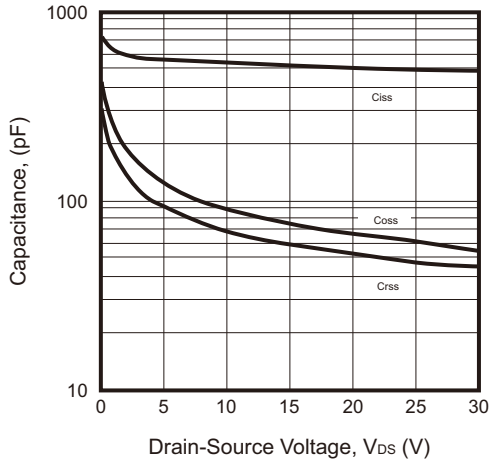


Fig.8 - Threshold Voltage vs Junction Temperature

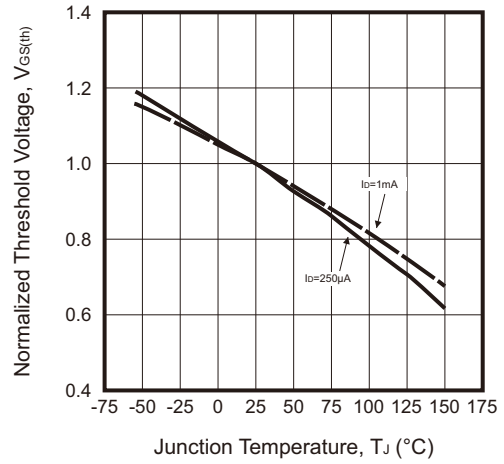


Fig.9 - Forward Transfer Admittance vs Drain Current

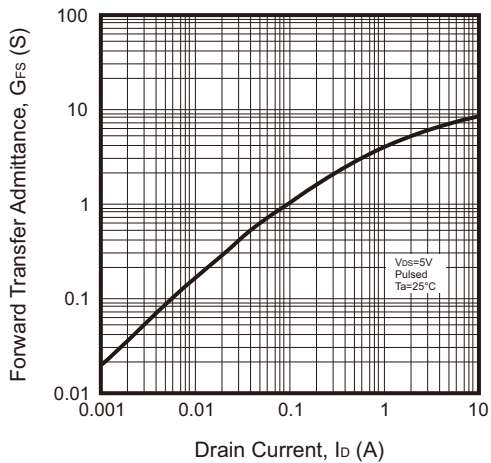


Fig.10 - Gate Charge Characteristics

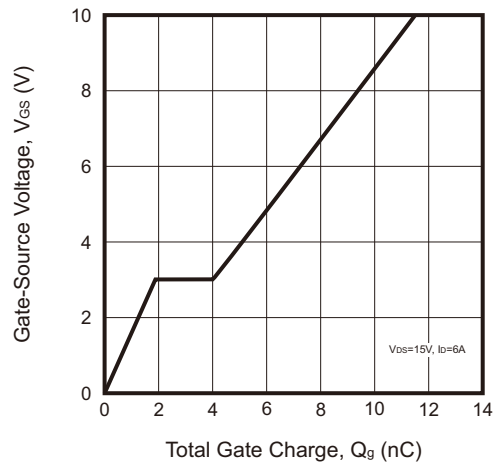


Fig.11 - Maximum Safe Operating Area

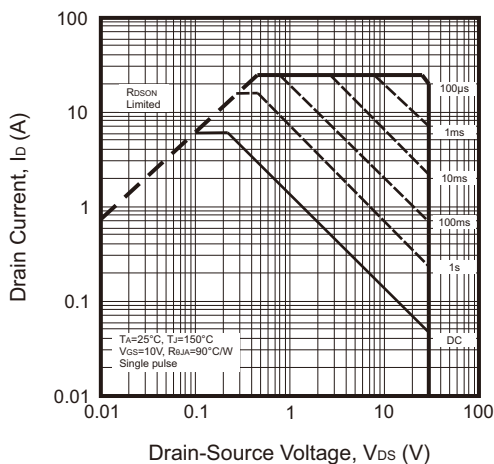
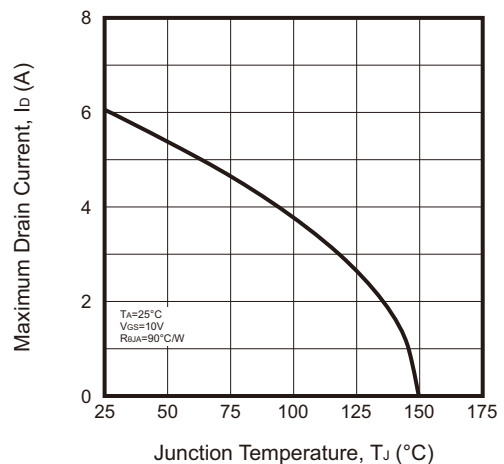


Fig.12 - Maximum Drain Current vs Junction Temperature



N-Channel Typical Rating and Characteristic Curves (CMSH9930Q8-HF)

Fig.13 - Single Pulse Power Rating, Junction to Ambient (Note on Page 1)

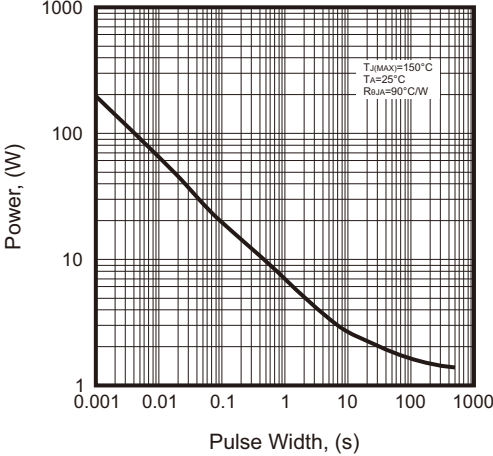
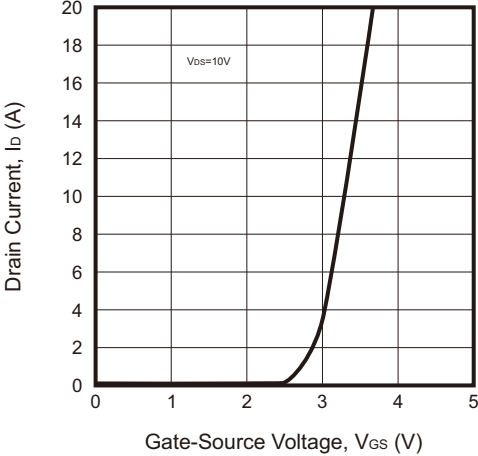


Fig.14 - Typical Transfer Characteristics



## P-Channel Typical Rating and Characteristic Curves (CMSh9930Q8-HF)

Fig.15 - Typical Output Characteristics

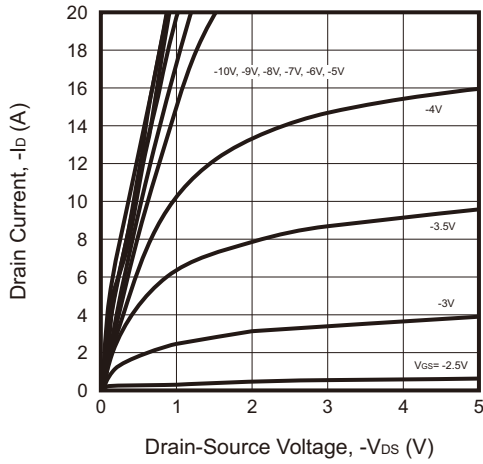


Fig.16 - Breakdown Voltage vs Ambient Temperature

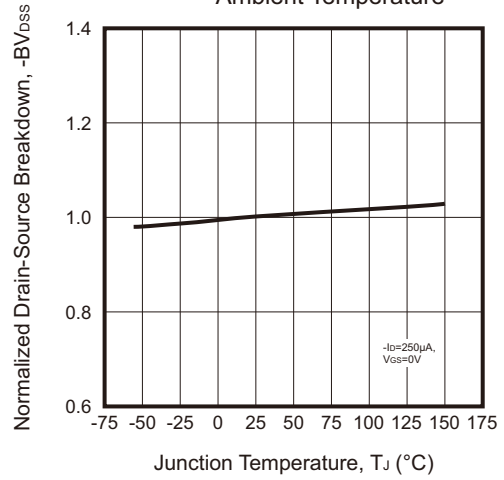


Fig.17 - Static Drain-Source On-State Resistance vs Drain Current

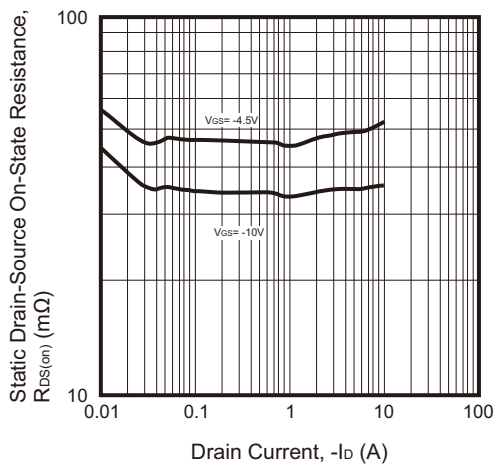


Fig.18 - Reverse Drain Current vs Source-Drain Voltage

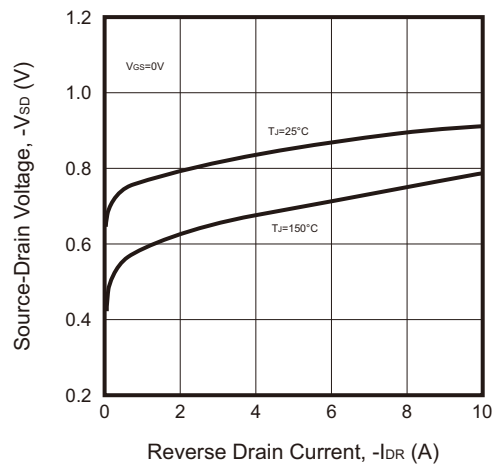


Fig.19 - Static Drain-Source On-State Resistance vs Gate-Source Voltage

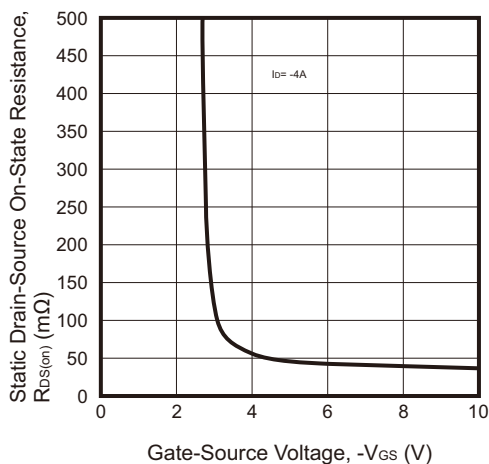
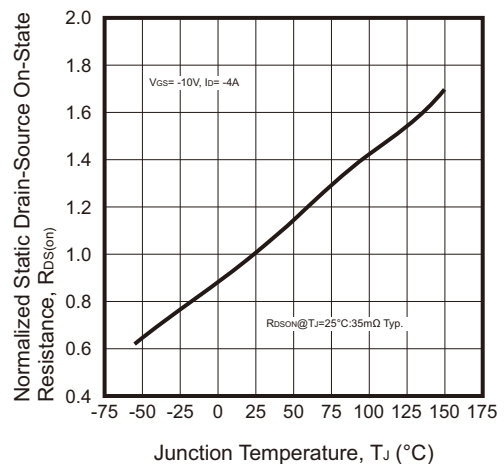


Fig.20 - Drain-Source On-State Resistance vs Junction Temperature



## P-Channel Typical Rating and Characteristic Curves (CMSh9930Q8-HF)

Fig.21 - Capacitance vs Drain-to-Source Voltage

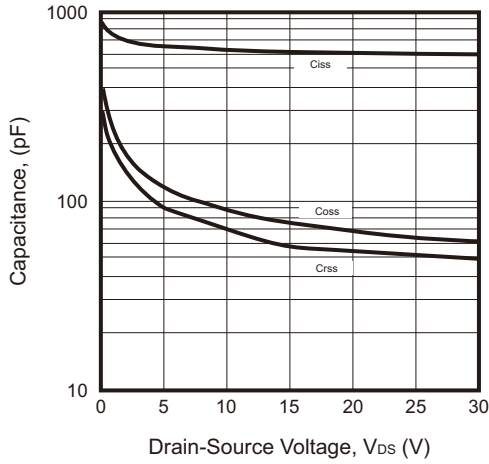


Fig.22 - Threshold Voltage vs Junction Temperature

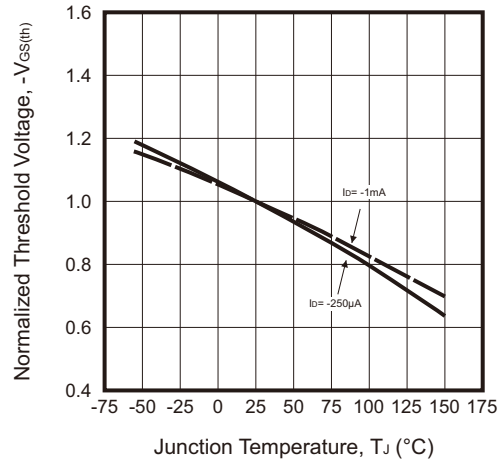


Fig.23 - Forward Transfer Admittance vs Drain Current

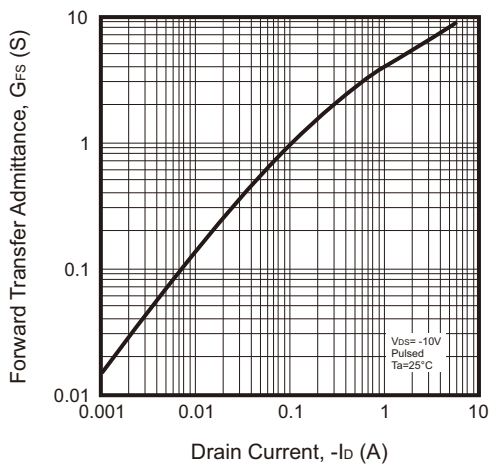


Fig.24 - Gate Charge Characteristics

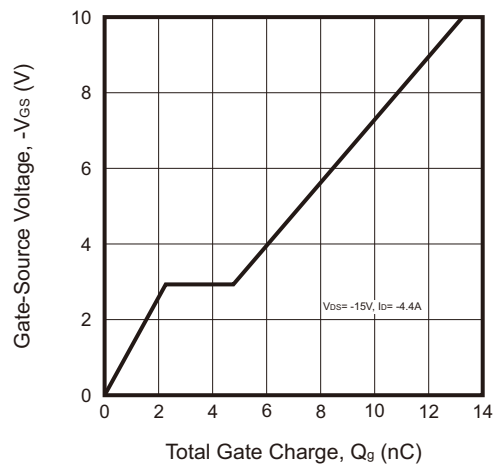


Fig.25 - Maximum Safe Operating Area

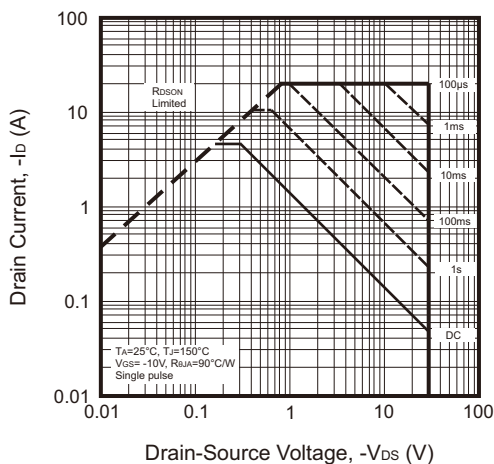
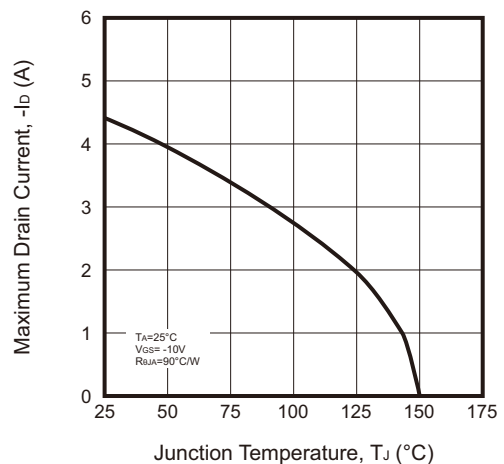


Fig.26 - Maximum Drain Current vs Junction Temperature





## P-Channel Typical Rating and Characteristic Curves (CMSH9930Q8-HF)

Fig.27 - Single Pulse Power Rating, Junction to Ambient (Note on Page 1)

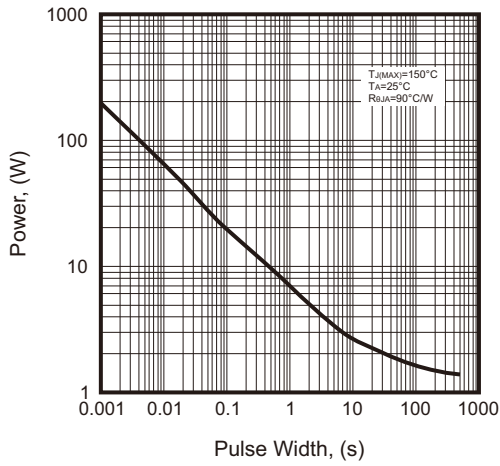
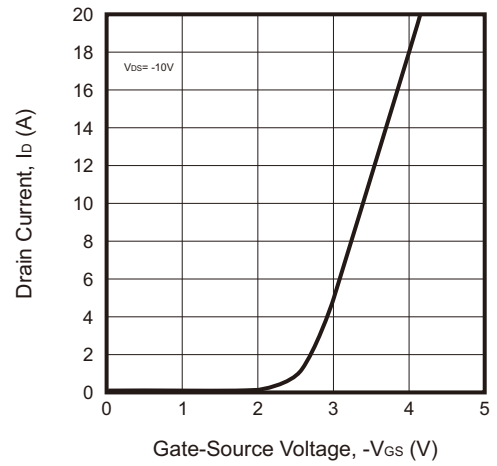
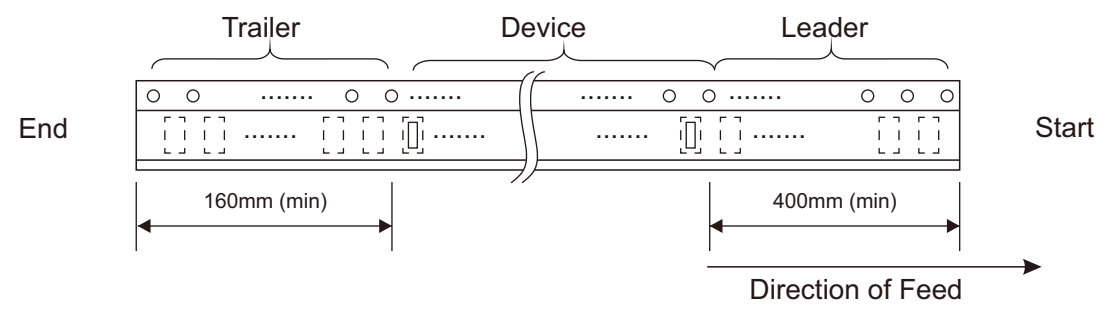
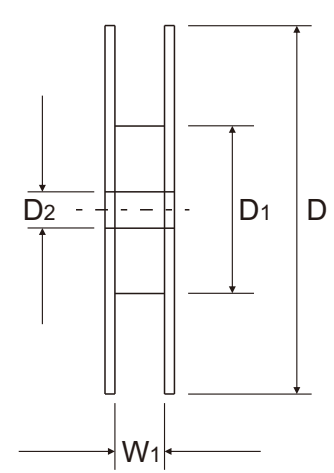
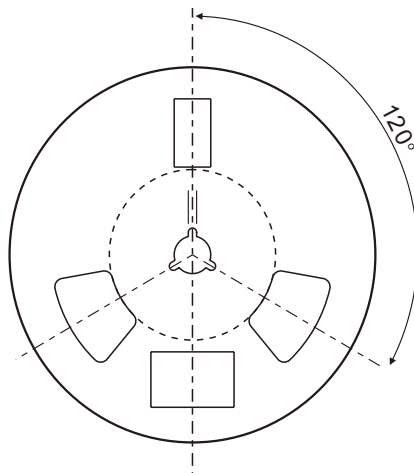
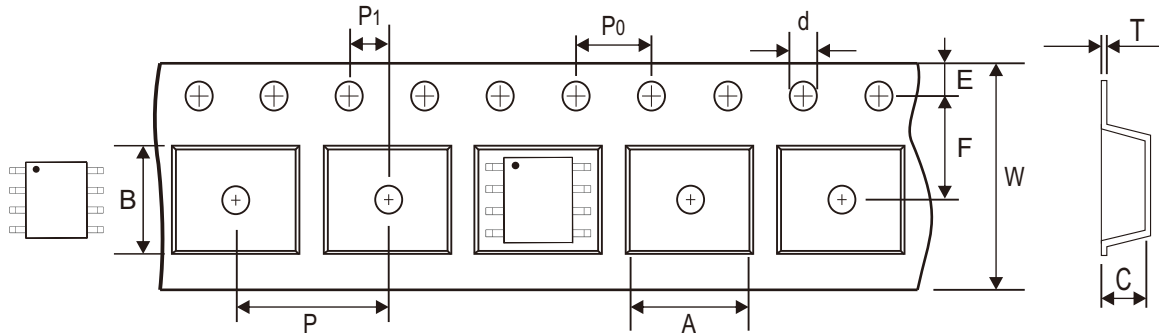


Fig.28 - Typical Transfer Characteristics



Reel Taping Specification

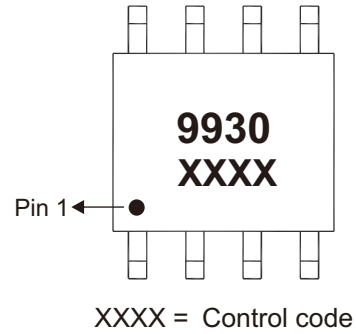


SOP-8	SYMBOL	A	B	C	d	D	D1	D2
	(mm)	6.40 ± 0.10	5.20 ± 0.10	2.10 ± 0.10	1.55 ± 0.05	330.00 ± 2.00	100.00 ± 1.50	13.50 ± 0.10
	(inch)	0.252 ± 0.004	0.205 ± 0.004	0.083 ± 0.004	0.061 ± 0.002	12.992 ± 0.079	3.937 ± 0.059	0.531 ± 0.004

SOP-8	SYMBOL	E	F	P	P0	P1	T	W	W1
	(mm)	1.75 ± 0.10	5.50 ± 0.05	8.00 ± 0.10	4.00 ± 0.10	2.00 ± 0.05	0.292 ± 0.013	12.00 + 0.30 - 0.10	13.40 ± 0.10
	(inch)	0.069 ± 0.004	0.217 ± 0.002	0.315 ± 0.004	0.157 ± 0.004	0.079 ± 0.002	0.011 ± 0.001	0.472 + 0.012 - 0.004	0.528 ± 0.004

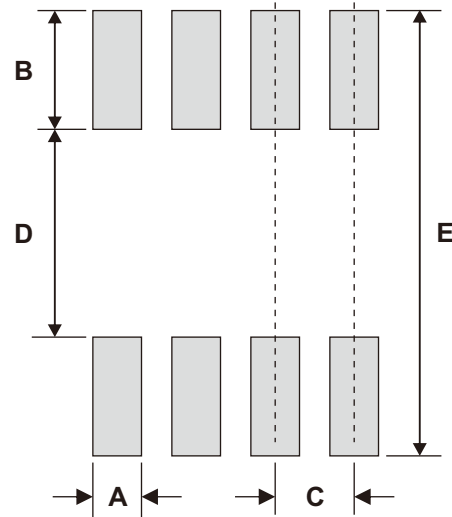
## Marking Code

Part Number	Marking Code
CMSH9930Q8-HF	9930



## Suggested P.C.B. PAD Layout

SIZE	SOP-8	
	(mm)	(inch)
A	0.60	0.024
B	1.52	0.060
C	1.27	0.050
D	4.00	0.157
E	7.00	0.276



## Standard Packaging

Case Type	REEL PACK	
	REEL ( pcs )	Reel Size (inch)
SOP-8	4,000	13